# Onsemi

# **Power Factor Correction** Controller

# **FAN7527B**

#### Description

The FAN7527B provides simple and high-performance active Power Factor Correction (PFC). The FAN7527B is optimized for electronic ballasts and low-power, high-density power supplies that require minimum board size, reduced external components, and low power dissipation. Because the R/C filter is included in the current-sense block, an external R/C filter is not necessary. Special circuitry prevents no-load runaway conditions. Regardless of the supply voltage, the output drive clamping circuit limits the overshoot of the power MOSFET gate drive, which improves system reliability.

#### Features

- Internal Startup Timer
- Internal R/C Filter Eliminates the Need for External R/C Filter
- Precise Adjustable Output Over-Voltage Protection
- Zero Current Detector
- One Quadrant Multiplier
- Trimmed 1.5% Internal Band Gap Reference
- Under-Voltage Lockout with 3 V of Hysteresis
- Totem–Pole Output with High–State Clamp
- Low Startup and Operating Current
- 8-Pin SOP or 8-Pin DIP
- These Devices are Pb-Free and are RoHS Compliant

#### Applications

- Electronic Ballast
- SMPS

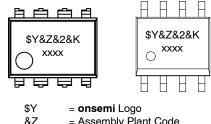




PDIP8 9.42x6.38, 2.54P CASE 646CM

SOIC8 CASE 751EB





= Assembly Plant Code

&2 = 2-Digit Date Code

&K = Lot Run Traceability Code

#### XXXX = Specific Device Code

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
FAN7527BN	PDIP8 (Pb-Free)	3000 / Tube
FAN7527BMX	SOIC8 (Pb-Free)	2500 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NOTE: Operating Temperature Range of both devices is -25 to +125°C

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#### **BLOCK DIAGRAM**

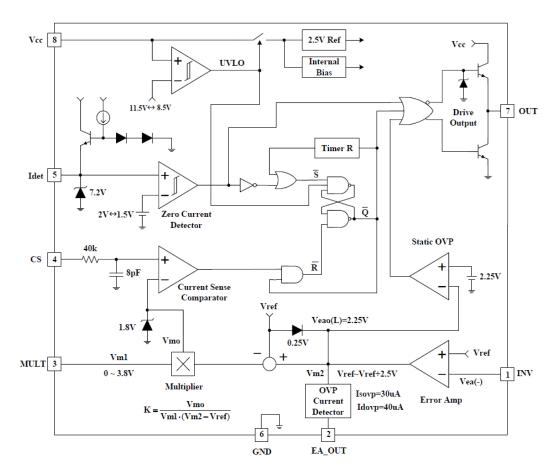


Figure 1. Block Diagram

# **PIN CONFIGURATION**

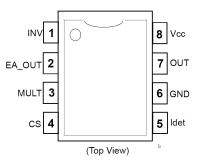


Figure 2. Pin Configuration

### **PIN DEFINITIONS**

Pin #	Name	Description
1	INV	Inverting input of the error amplifier. The output of the boost converter should be resistively divided to 2.5 V and connected to this pin.
2	EA_OUT	Output of the error amplifier. Feedback compensation network is placed between this pin and the INV pin.
3	MULT	Input to the multiplier stage. The full-wave rectified AC voltage is divided to less than 2 V and is connected to this pin.
4	CS	Input of the PWM comparator. The MOSFET current is sensed by a resistor and the resulting voltage is applied to this pin. An internal R/C filter is included to reject high-frequency noise
5	ldet	Zero Current Detection (ZCD) input
6	GND	Ground
7	OUT	Gate driver output. Push-pull output stage is able to drive the power MOSFET with a peak current of 500 mA
8	V <sub>CC</sub>	Supply voltage of driver and control circuits

#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter			Max.	Unit
Vcc	Supply Voltage			30	V
Ioh, Iol	Peak Drive Output Current			±500	mA
ICLAMP	Driver Output Clamping Diodes $V_O > V_{CC}$ or $V_O < -0.3$ V			±10	mA
IDET	Detector Clamping Diodes			±10	mA
VIN	Error Amplifier Multiplier and Comparator Input Voltages		-0.3	6.0	V
TJ	Operation Junction Temperature			+150	°C
Topr	Operating Temperature Range		-25	+125	°C
Тѕтс	Storage Temperature Range		-65	+150	°C
PD	Power Dissipation	SOIC8		0.8	W
		PDIP8		1.1	W
Θја	Thermal Resistance Junction-Ambient	SOIC8		150	°C/W
		PDIP8		110	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## **TEMPERATURE CHARACTERISTICS**

 $(-25^\circ C \leq T_A \leq 125^\circ C)$ 

Symbol	Parameter		Тур.	Max.	Unit
$\Delta VREF$	Temperature Stability Reference Voltage (V <sub>REF</sub> )		20		mV
ΔΚ/ΔΤ	T Temperature Stability for Multiplier Gain (K)		-0.2		% / °C

#### **ELECTRICAL CHARACTERISTICS**

(V\_{CC} = 14 V, –25°C  $\leq$  T\_A  $\leq$  125°C, unless otherwise stated.)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
UNDER-VOL				-	i	i
Vth(st)	Start Threshold Voltage	V <sub>CC</sub> Increasing	10.5	11.5	12.5	V
HY(st)	UVLO Hysteresis		2	3	4	V
SUPPLY CUP	RENT SECTION			1	1	1
Isт	Startup Supply Current	$V_{CC} = V_{th(st)} - 0.2 V$	10	60	100	μΑ
lcc	Operating Supply Current	Output Not Switching		3	6	mA
ICC(OVP)	Operating Current at OVP	V <sub>INV</sub> = 3 V		1.7	4.0	mA
IDCC	Dynamic Operating Supply Current	50 kHz, C <sub>I</sub> = 1 nF		4	8	mA
ERROR AMP	LIFIER SECTION				-	-
VREF	Voltage Feedback Input Threshold	$I_{REF}$ = 0 mA, $T_A$ = 25°C	2.465	2.500	2.535	V
		$25^{\circ}C \le T_A \le 125^{\circ}C$	2.440	2.500	2.560	
$\Delta V$ FEF1	Line Regulation	$14~V \leq V_{CC} \leq 25~V$		0.1	10.0	mV
$\Delta V$ FEF3	Temperature Stability of V <sub>REF</sub> (Note 1)	$-25^\circ C \leq T_A \leq 125^\circ C$		20		mV
lb(ea)	Input Bias Current		-0.5		0.5	μΑ
ISOURCE	Output Source Current	V <sub>M2</sub> = 4 V	-2	-4		mA
Isink	Output Sink Current	V <sub>M2</sub> = 4 V	2	4		mA
VEAO(H)	Output Upper Clamp Voltage (Note 1)	I <sub>SOURCE</sub> = 0.1 mA		6		V
VEAO(L)	Output Lower Clamp Voltage (Note 1)	I <sub>SINK</sub> = 0.1 mA		2.25		V
G <sub>V</sub>	Large Signal Open-Loop Gain (Note 1)		60	80		dB
PSRR	Power Supply Rejection Ratio (Note 1)	$14~V \leq V_{CC} \leq 25~V$	60	80		dB
GBW	Unity Gain Bandwidth (Note 1)			1		MHz
SR	Slew Rate (Note 1)			0.6		V/μs
MULTIPLIER	SECTION					-
lb(m)	Input Bias Current (Pin 3)		-0.5		0.5	μΑ
$\Delta V_{M1}$	M1 Input Voltage Range (Pin 3)				3.8	V
$\Delta V_{M2}$	M2 Input Voltage Range (Pin 2)		VREF		V <sub>REF</sub> +2.5	V
К	Multiplier Gain (Note 1)	V <sub>M1</sub> = 1 V, V <sub>M2</sub> = 3.5 V	0.36	0.44	0.52	1 / V
VOMAX(m)	Maximum Multiplier Output Voltage	$V_{INV} = 0 V, V_{M1} = 4 V$	1.65	1.80	1.95	V
$\Delta K / \Delta T$	Temperature Stability of K (Note 1)	$-25^\circ C \leq T_A \leq 125^\circ C$		-0.2		% / °C
CURRENT SI	ENSE SECTION			-	_	-
VIO(CS)	Input Offset Voltage (Note 1)	$V_{M1} = 0 V, V_{M2} = 2.2 V$	-10	3	10	mV
lb(CS)	Input Bias Current	$0~V \leq V_{CS} \leq 1.7~V$	-1.0	-0.1	1.0	μΑ
tD(CS)	Current Sense Delay to Output (Note 1)			200	500	ns
ZERO CURR	ENT DETECT SECTION					
VTH(DET)	Input Voltage Threshold	V <sub>DET</sub> Increasing	1.7	2.0	2.3	V
HY(DET)	Detect Hysteresis		0.2	0.5	0.8	V
VCLAMP(I)	Input Low Clamp Voltage	I <sub>DET</sub> = -100 μA	0.45	0.75	1.00	V
VCLAMP(H)	Input High Clamp Voltage	I <sub>DET</sub> = 3 mA	6.5	7.2	7.9	V

#### ELECTRICAL CHARACTERISTICS (continued)

(V<sub>CC</sub> = 14 V,  $-25^{\circ}C \le T_A \le 125^{\circ}C$ , unless otherwise stated.)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit		
ZERO CURRENT DETECT SECTION								
lb(DET)	Input Bias Current	$1 \text{ V} \leq \text{V}_{\text{DET}} \leq 5 \text{ V}$	-1.0	-0.1	1.0	μA		
ICLAMP(D)	Input High/Low Clamp Diode Current (Note 1)				±3	mA		
OUTPUT SEC	DUTPUT SECTION							
Vон	Output Voltage High	I <sub>O</sub> = –10 mA	10.5	11.0		V		
Vol	Output Voltage Low	l <sub>O</sub> = 10 mA		0.8	1.0	V		
t <sub>R</sub>	Rising Time (Note 1)	C <sub>L</sub> = 1 nF		130	200	ns		
t <sub>F</sub>	Falling Time (Note 1)	C <sub>L</sub> = 1 nF		50	120	ns		
Vomax(0)	Maximum Output Voltage	$V_{CC}$ = 20 V, $I_{O}$ = 100 $\mu$ A	12	14	16	V		
VOMIN(O)	Output Voltage with UVLO Activated	V <sub>CC</sub> = 5 V, I <sub>O</sub> = 100 μA			1	V		
RESTART TIM	RESTART TIMER SECTION							
tD(RST)	Restart Time Delay	V <sub>M1</sub> = 1 V, V <sub>M2</sub> = 3.5 V		150		μs		
OVER-VOLT	OVER-VOLTAGE PROTECTION SECTION							
ISOVP	Soft OVP Detecting Current		25	30	35	μA		
IDOVP	Dynamic OVP Detecting Current		35	40	45	μA		
Vovp	Static OVP Threshold Voltage	V <sub>INV</sub> = 2.7 V	2.10	2.25	2.40	V		

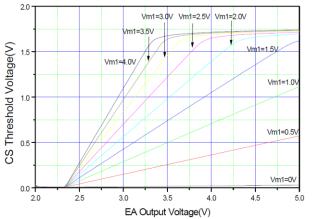
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. These parameters, although guaranteed, are not 100% tested in production.

Multiplier Gain:

$$\mathsf{K} = \frac{\mathsf{Pin4}\_\mathsf{Threshold}}{\mathsf{V}_{\mathsf{M1}} \times \left(\mathsf{V}_{\mathsf{M2}} - \mathsf{V}_{\mathsf{REF}}\right)}$$

where  $V_{M1} = V_{PIN3}$ ,  $V_{M2} = V_{PIN2}$ 

## **TYPICAL PERFORMANCE CHARACTERISTICS**





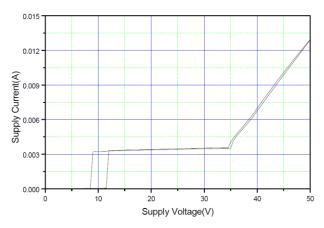


Figure 5. Supply Current vs. Supply Voltage

14 12.

10-

8-6. 4. 2-

Startup Threshold(V)

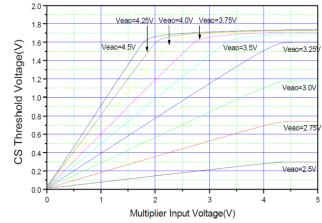


Figure 4. Multiplier Input Voltage vs. Current Sensing Threshold

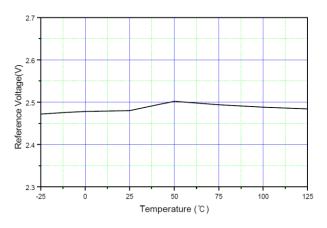
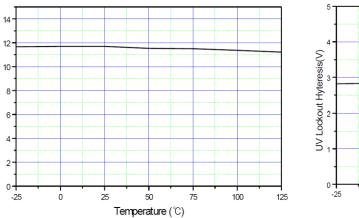


Figure 6. Reference Voltage vs. Temperature





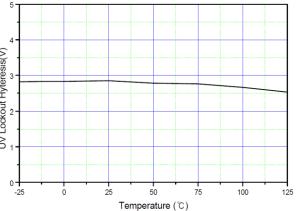


Figure 8. UVLO Hysteresis vs. Temperature

# TYPICAL PERFORMANCE CHARACTERISTICS (continued)

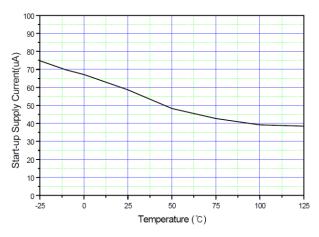


Figure 9. Startup Supply Current vs. Temperature

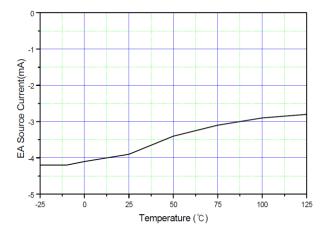


Figure 10. Error Amplifier Source Current

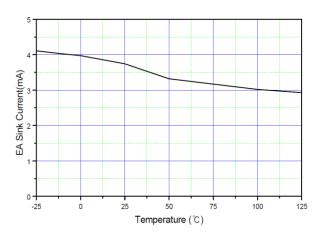


Figure 11. Error Amplifier Sink Current vs. Temperature

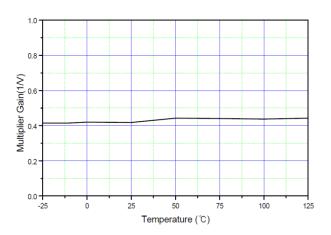
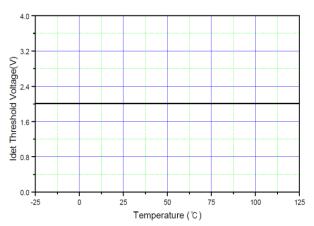


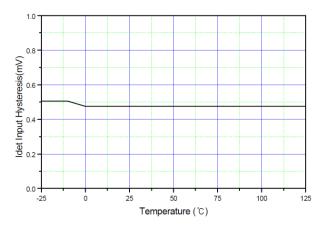


Figure 12. Error Amplifier Input Bias Current vs. Temperature





# TYPICAL PERFORMANCE CHARACTERISTICS (continued)



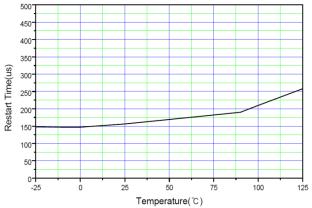


Figure 15. IDET Input Hysteresis vs. Temperature



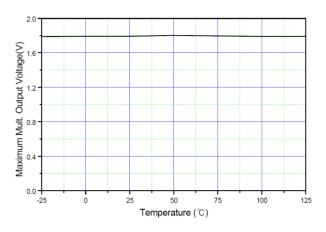


Figure 17. Maximum Multiplier Output Voltage vs. Temperature

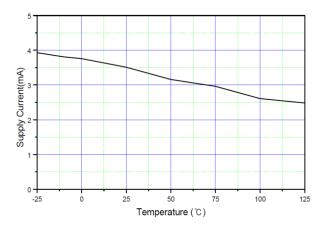
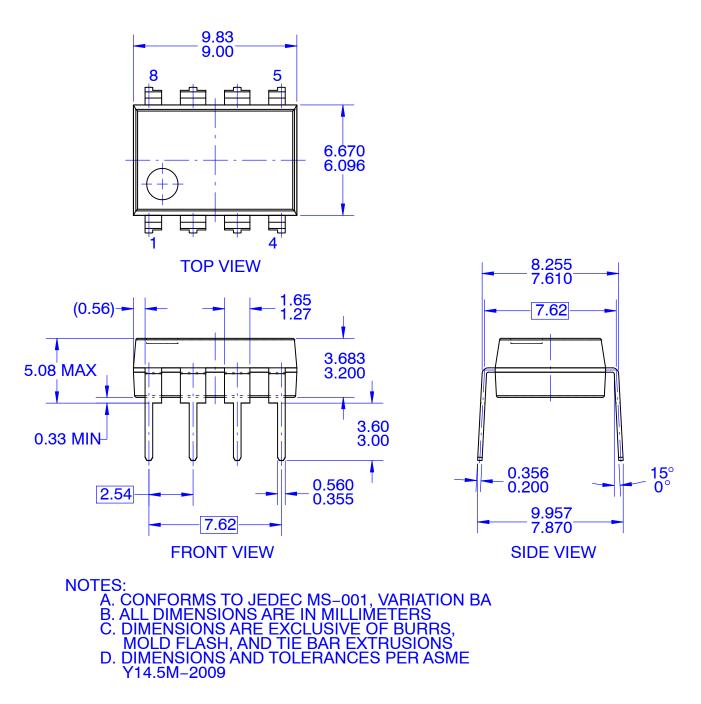


Figure 18. Supply Current vs. Temperature



PDIP8 9.42x6.38, 2.54P CASE 646CM ISSUE O

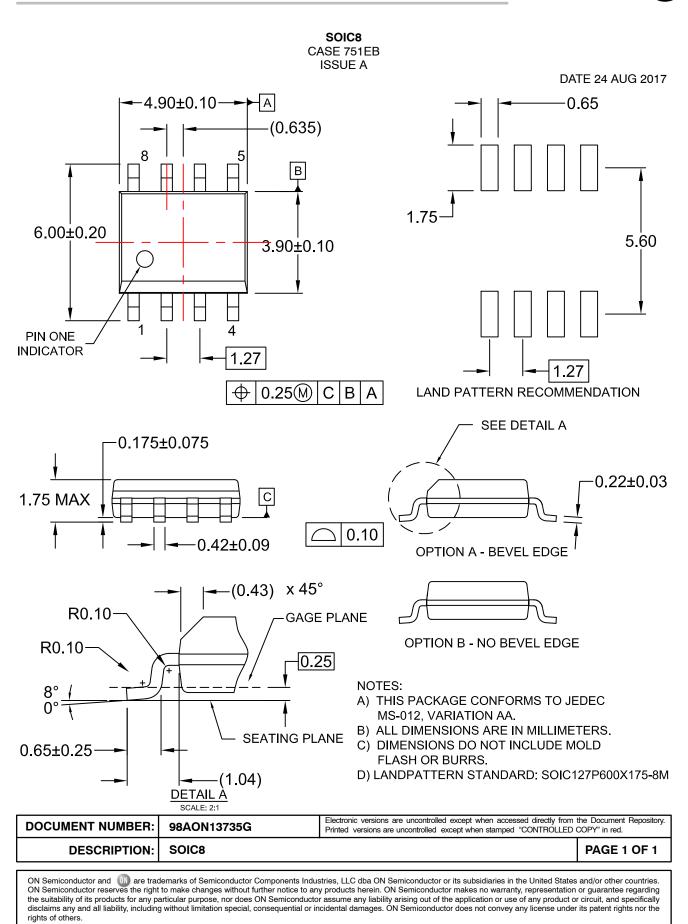
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